2SD1937

Silicon NPN epitaxial planer type

For low-frequency amplification Complementary to 2SB1297

Features

- High collector to emitter voltage V_{CEO}.
- Optimum for the driver-stage of a low-frequency and 40 to 60W output amplifier.
- Allowing supply with the radial taping.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	120	V
Collector to emitter voltage	V_{CEO}	120	V
Emitter to base voltage	V _{EBO}	5	V
Peak collector current	I_{CP}	1	A
Collector current	$I_{\rm C}$	0.5	A
Collector power dissipation	P_{C}	1	W
Junction temperature	T_j	150	°C
Storage temperature	$T_{ m stg}$	−55 ~ +150	°C

Unit: mm 5.9±0.2 4.9±0.2 0.45^{+0.2} 1.Emitter 2:Collector 3:Base TO-92L-A1 Package

■ Electrical Characteristics (Ta=25°C)

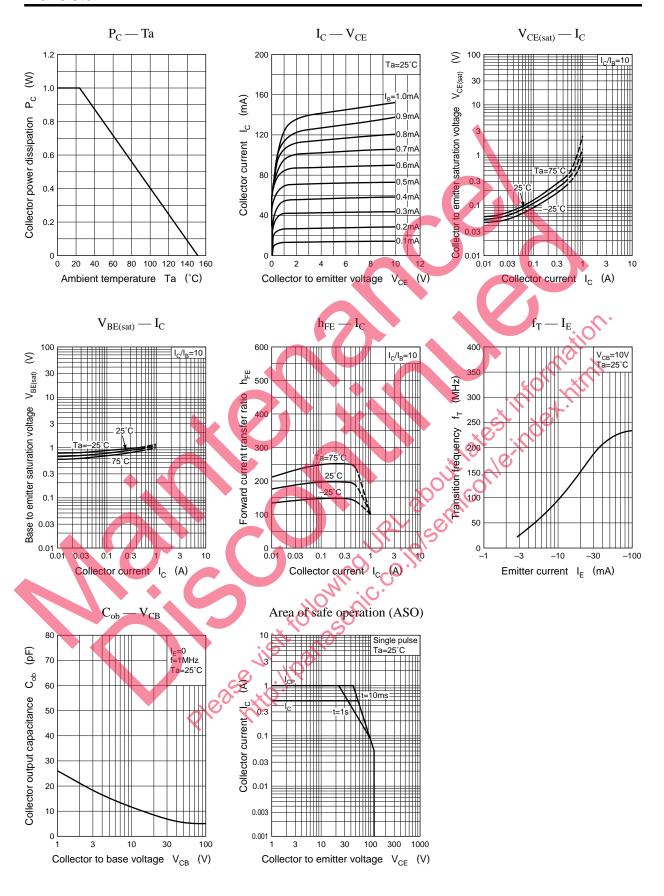
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = 0.1 \text{mA}, I_{\rm B} = 0$	120			V
Emitter to base voltage	V _{EBO}	$I_{\rm E} = 10 \mu {\rm A}, I_{\rm C} = 0$	5			V
Forward current transfer ratio	h _{FE1} *	$V_{CE} = 10V, I_{C} = 150mA$	130		330	
	h _{FE2}	$V_{\rm CE} = 5 \text{V}, I_{\rm C} = 500 \text{mA}$	50			
Collector to emitter saturation voltage	V _{CE(sat)}	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$			1	V
Base to emitter saturation voltage	V _{BE(sat)}	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$			1.2	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -50mA, f = 200MHz$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$			20	pF

*h_{FE1} Rank classification

Rank	R	S
h _{FE1}	130 ~ 220	185 ~ 330

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Transistor 2SD1937



Panasonic 643

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